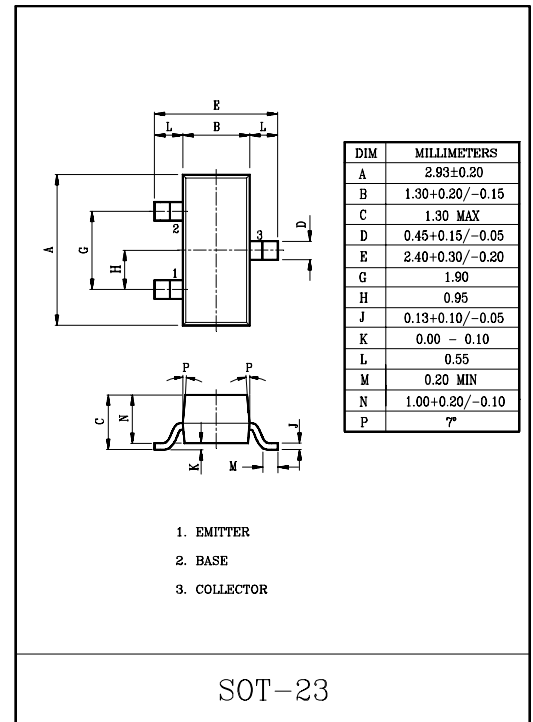
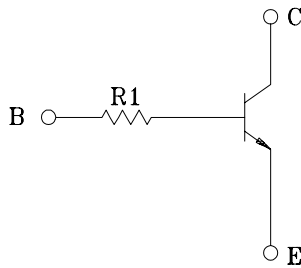


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

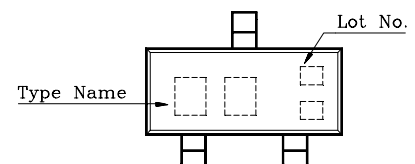
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	100	nA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	100	nA
DC Current Gain		h_{FE}	$V_{CE}=5V, I_C=1mA$	120	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$	-	0.1	0.3	V
Transition Frequency		f_T *	$V_{CE}=10V, I_C=5mA$	-	250	-	MHz
Input Resistor	KRC110S	R_1		-	4.7	-	kΩ
	KRC111S			-	10	-	
	KRC112S			-	100	-	
	KRC113S			-	22	-	
	KRC114S			-	47	-	

Note : * Characteristic of Transistor Only

MARK SPEC

TYPE	KRC110S	KRC111S	KRC112S	KRC113S	KRC114S
MARK	NK	NM	NN	NO	NP

Marking



KRC110S ~ KRC114S

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC			SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Switching Time	Rise Time	KRC110S	t_r	$V_O=5V$ $V_{IN}=5V$ $R_L=1k\Omega$	–	0.025	–	μS
		KRC111S			–	0.03	–	
		KRC112S			–	0.3	–	
		KRC113S			–	0.06	–	
		KRC114S			–	0.11	–	
	Storage Time	KRC110S	t_{stg}		–	3.0	–	
		KRC111S			–	2.0	–	
		KRC112S			–	6.0	–	
		KRC113S			–	4.0	–	
		KRC114S			–	5.0	–	
	Fall Time	KRC110S	t_f		–	0.2	–	
		KRC111S			–	0.12	–	
		KRC112S			–	2.0	–	
		KRC113S			–	0.9	–	
		KRC114S			–	1.4	–	